

## NCE N-Channel Super Trench II Power MOSFET

### Description

The NCEP018N60AGU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

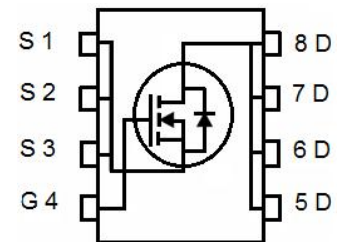
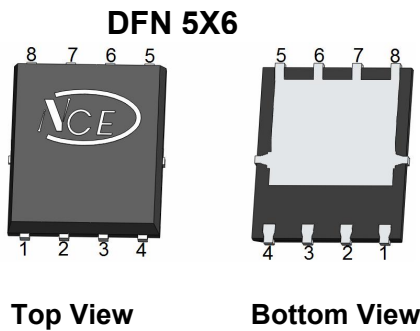
### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS} = 60V, I_D = 195A$   
 $R_{DS(ON)} = 1.4\ m\Omega$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 1.8\ m\Omega$  (typical) @  $V_{GS} = 4.5V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100% ΔVds TESTED!**



Schematic Diagram

### Package Marking and Ordering Information

| Device Marking | Device        | Device Package | Reel Size | Tape width | Quantity |
|----------------|---------------|----------------|-----------|------------|----------|
| P018N60AGU     | NCEP018N60AGU | DFN5X6-8L      | -         | -          | -        |

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

| Parameter   | Symbol             | Limit      | Unit |
|---|--------------------|------------|------|
| Drain-Source Voltage                              | $V_{DS}$           | 60         | V    |
| Gate-Source Voltage                               | $V_{GS}$           | ±20        | V    |
| Drain Current-Continuous                          | $I_D$              | 195        | A    |
| Drain Current-Continuous( $T_c = 100^\circ C$ )   | $I_D(100^\circ C)$ | 135        | A    |
| Pulsed Drain Current                              | $I_{DM}$           | 780        | A    |
| Maximum Power Dissipation                         | $P_D$              | 220        | W    |
| Derating factor                                   |                    | 1.76       | W/°C |
| Single pulse avalanche energy <sup>(Note 1)</sup> | $E_{AS}$           | 871        | mJ   |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$     | -55 To 150 | °C   |

### Thermal Characteristic

|   |                 |      |      |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case                        | $R_{\theta JC}$ | 0.57 | °C/W |
| Thermal Resistance, Junction-to-Ambient <sup>(Note 4)</sup> | $R_{\theta JA}$ | 50   | °C/W |

## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

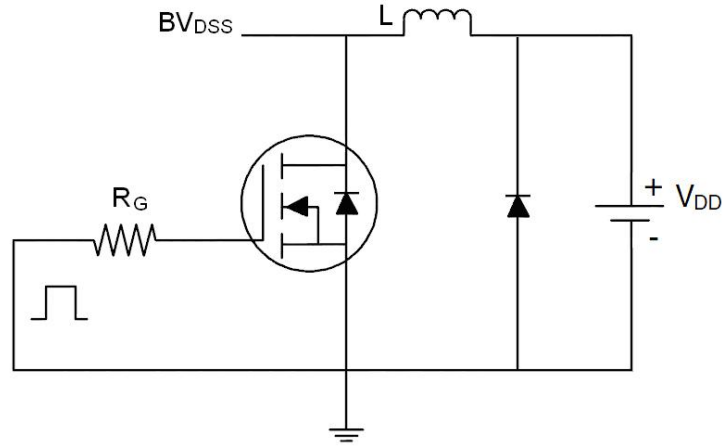
| Parameter                                 | Symbol              | Condition   | Min | Typ  | Max  | Unit |
|---|---------------------|---|-----|------|------|------|
| <b>Off Characteristics</b>                |                     |   |     |      |      |      |
| Drain-Source Breakdown Voltage            | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA  | 60  |      | -    | V    |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V   | -   | -    | 1    | μA   |
| Gate-Body Leakage Current                 | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V  | -   | -    | ±100 | nA   |
| <b>On Characteristics</b>                 |                     |   |     |      |      |      |
| Gate Threshold Voltage                    | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                | 1.0 | 1.7  | 2.5  | V    |
| Drain-Source On-State Resistance          | R <sub>DS(on)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =20A   | -   | 1.4  | 1.8  | mΩ   |
|   |                     | V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A  | -   | 1.8  | 2.4  | mΩ   |
| Forward Transconductance                  | g <sub>FS</sub>     | V <sub>DS</sub> =5V, I <sub>D</sub> =20A  | -   | 50   | -    | S    |
| <b>Dynamic Characteristics</b>            |                     |   |     |      |      |      |
| Input Capacitance                         | C <sub>iss</sub>    | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,<br>F=1.0MHz                                  | -   | 6150 | -    | PF   |
| Output Capacitance                        | C <sub>oss</sub>    |   | -   | 965  | -    | PF   |
| Reverse Transfer Capacitance              | C <sub>rss</sub>    |   | -   | 65   | -    | PF   |
| <b>Switching Characteristics</b> (Note 2) |                     |   |     |      |      |      |
| Turn-on Delay Time                        | t <sub>d(on)</sub>  | V <sub>DD</sub> =30V, I <sub>D</sub> =20A<br>V <sub>GS</sub> =10V, R <sub>G</sub> =4.7Ω | -   | 17   | -    | nS   |
| Turn-on Rise Time                         | t <sub>r</sub>      |   | -   | 10   | -    | nS   |
| Turn-Off Delay Time                       | t <sub>d(off)</sub> |   | -   | 60   | -    | nS   |
| Turn-Off Fall Time                        | t <sub>f</sub>      |   | -   | 18   | -    | nS   |
| Total Gate Charge                         | Q <sub>g</sub>      | V <sub>DS</sub> =30V, I <sub>D</sub> =20A,<br>V <sub>GS</sub> =10V                      | -   | 103  |      | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>     |   | -   | 18   |      | nC   |
| Gate-Drain Charge                         | Q <sub>gd</sub>     |   | -   | 15.5 |      | nC   |
| <b>Drain-Source Diode Characteristics</b> |                     |   |     |      |      |      |
| Diode Forward Voltage                     | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =20A  | -   |      | 1.2  | V    |
| Diode Forward Current                     | I <sub>S</sub>      |   | -   | -    | 195  | A    |
| Reverse Recovery Time                     | t <sub>rr</sub>     | T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub><br>di/dt = 100A/μs               | -   | 60   |      | nS   |
| Reverse Recovery Charge                   | Q <sub>rr</sub>     |   | -   | 85   |      | nC   |

### Notes:

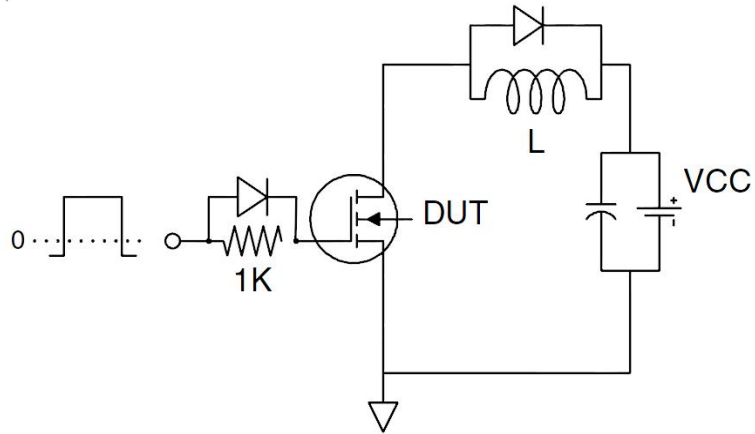
- EAS condition : T<sub>j</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
- Guaranteed by design, not subject to production
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J</sub>(MAX)=150°C. The SOA curve provides a single pulse rating.
- The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25° C. The maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

## Test Circuit

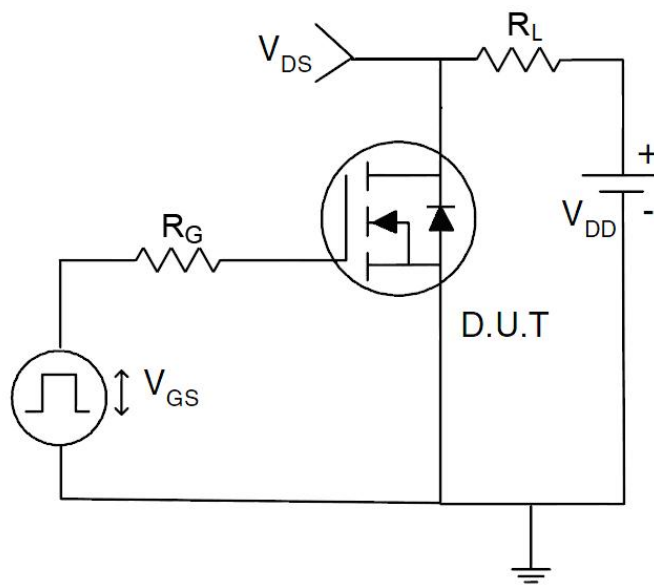
### 1) E<sub>AS</sub> test Circuit



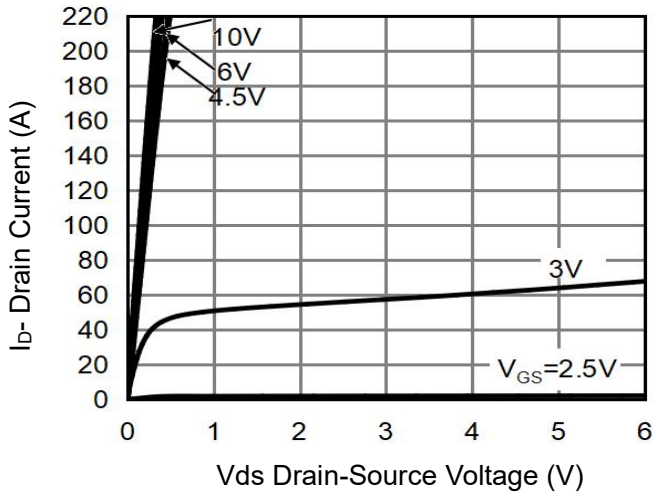
### 2) Gate charge test Circuit



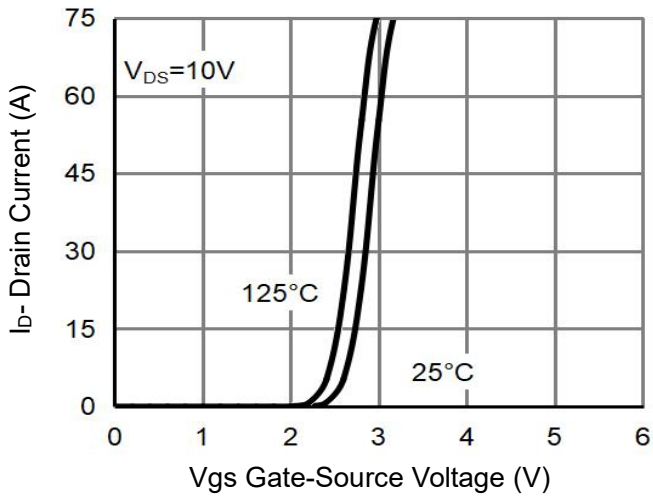
### 3) Switch Time Test Circuit



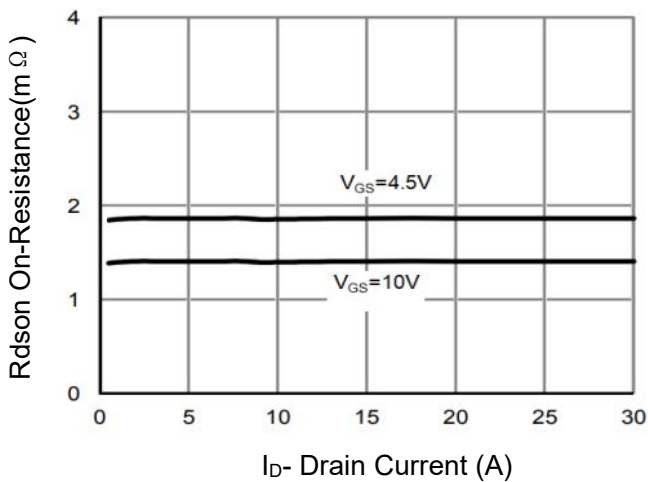
## Typical Electrical and Thermal Characteristics



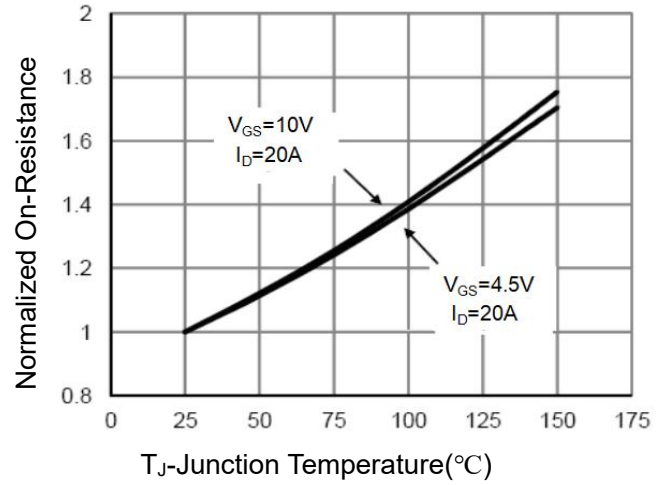
**Figure 1 Output Characteristics**



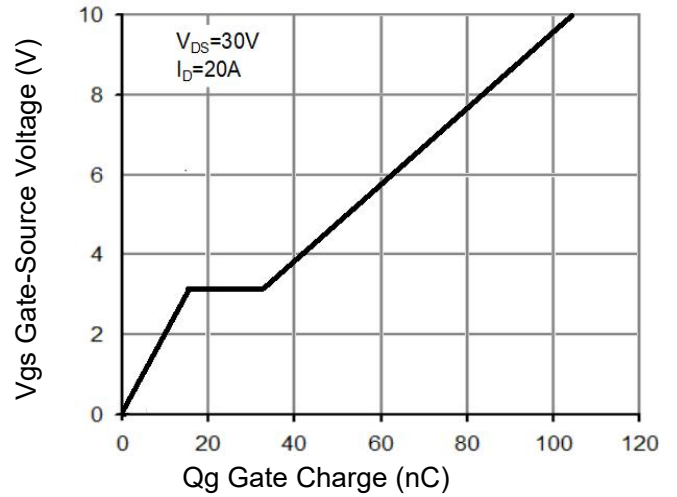
**Figure 2 Transfer Characteristics**



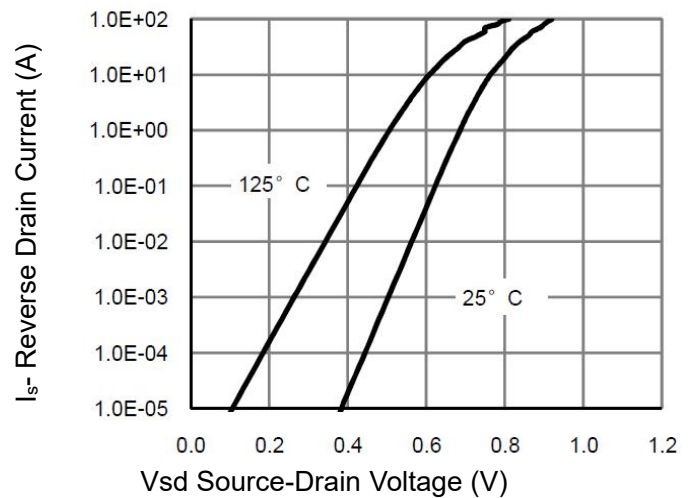
**Figure 3 Rdson- Drain Current**



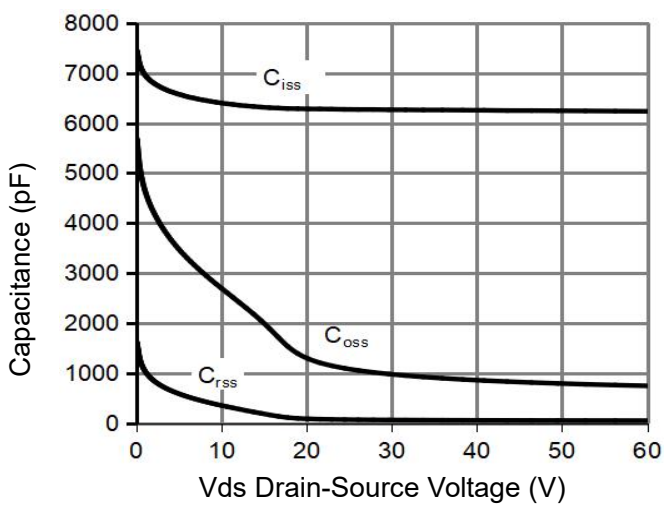
**Figure 4 Rdson-Junction Temperature**



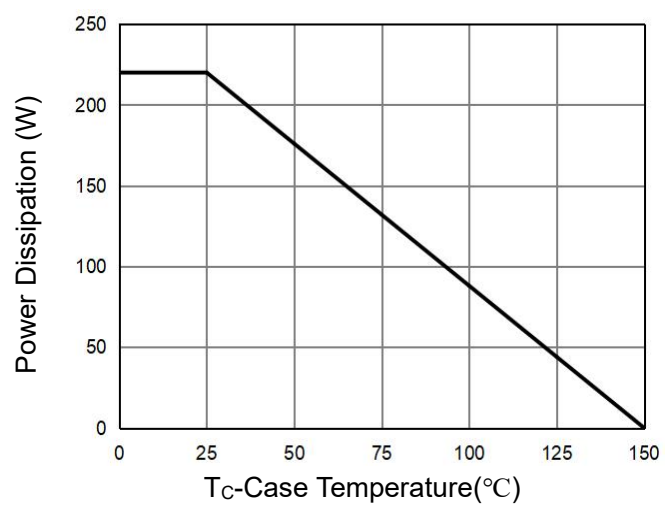
**Figure 5 Gate Charge**



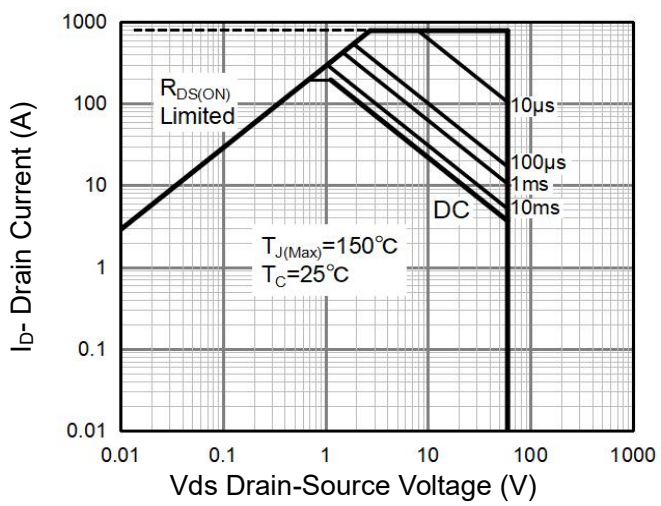
**Figure 6 Source- Drain Diode Forward**



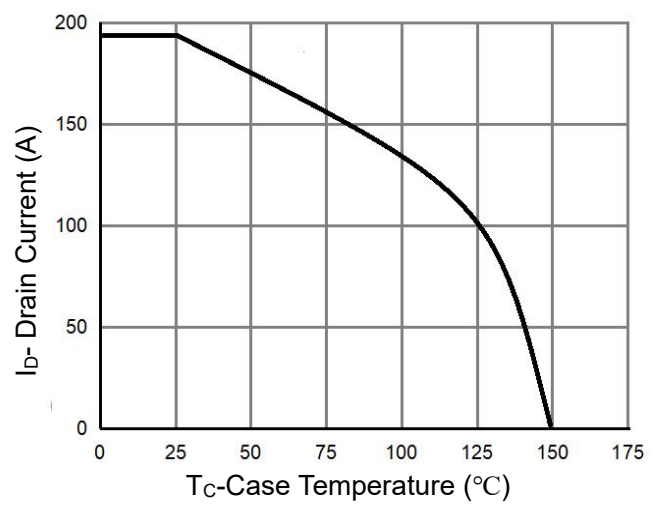
**Figure 7 Capacitance vs Vds**



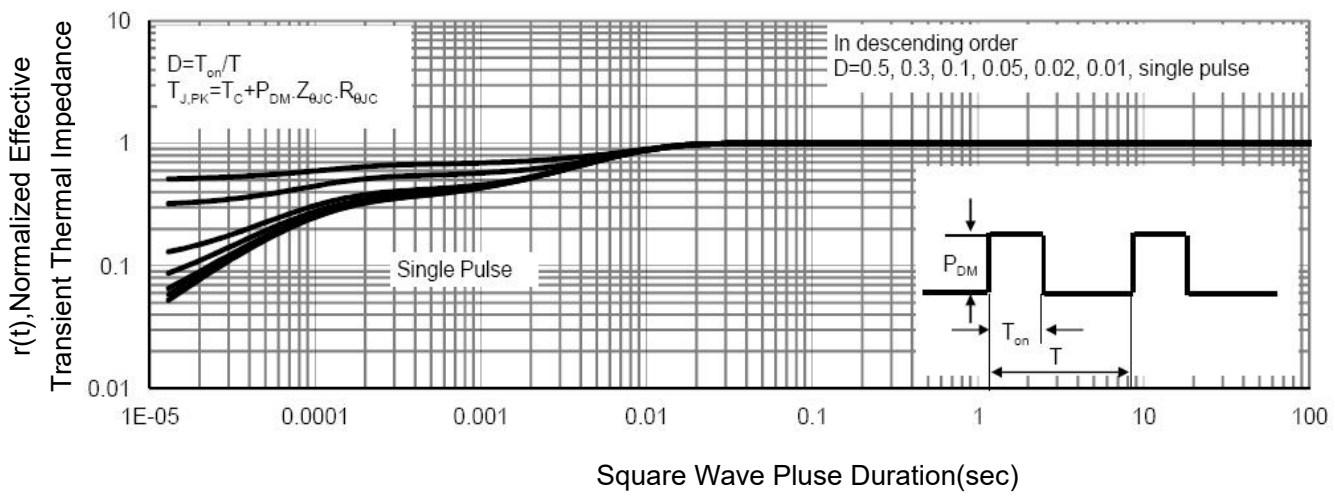
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area** (Note 3)

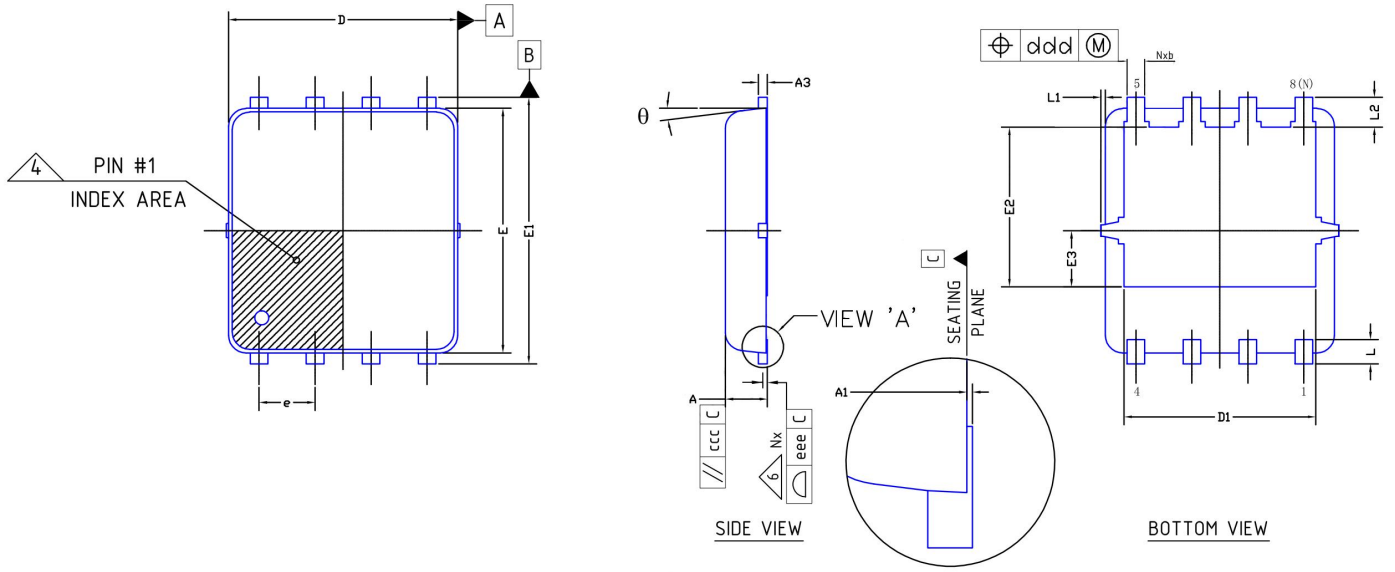


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information



| Thickness Symbol | Dimension Table |         |         | NOTE |
|------------------|-----------------|---------|---------|------|
|                  | MINIMUM         | NOMINAL | MAXIMUM |      |
| A                | 0.85            | 0.95    | 1.00    |      |
| A1               | 0.00            | ---     | 0.05    |      |
| A3               | ---             | 0.2 Ref | ---     |      |
| b                | 0.30            | 0.40    | 0.50    |      |
| D                | 5.20 BSC        |         |         |      |
| E                | 5.55 BSC        |         |         |      |
| e                | 1.27 BSC        |         |         |      |
| D1               | 4.25            | 4.35    | 4.45    |      |
| E1               | 5.95            | 6.05    | 6.15    |      |
| E2               | 3.525           | 3.625   | 3.725   |      |
| E3               | 1.175           | 1.275   | 1.375   |      |
| L                | 0.45            | 0.55    | 0.65    |      |
| L1               | 0               | ---     | 0.15    |      |
| L2               | 0.68 REF        |         |         |      |
| θ                | 0°              | ---     | 10°     |      |
| aaa              | 0.05            |         |         |      |
| bbb              | 0.10            |         |         |      |
| ccc              | 0.10            |         |         |      |
| ddd              | 0.05            |         |         |      |
| eee              | 0.08            |         |         |      |
| N                | 8               |         |         | 3    |
| ND               | 4               |         |         | 5    |
| NOTES            | 1,2             |         |         |      |
| LF PART NO.      | 445831/445897   |         |         |      |

NOTE:

1. Dimensioning and tolerancing conform to ASME Y14.5-2009.
2. All dimensions are in millimeters.
3. N is the total number of terminals.
4. The location of the marked terminal #1 identifier is within the hatched area.
5. NE refers to the maximum number of terminals E side.
6. Coplanarity applies to the terminals and all other bottom surface metallization.

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